



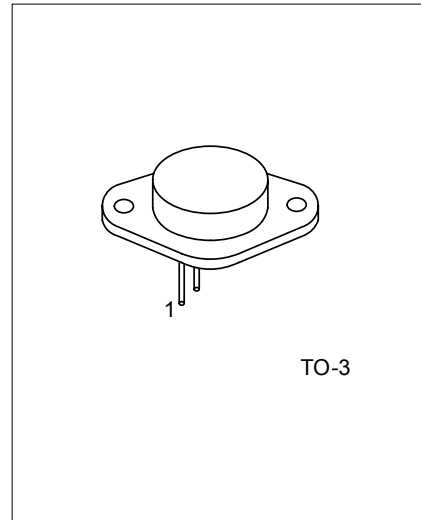
2N2955

PNP SILICON TRANSISTOR

SILICON PNP TRANSISTORS

■ **DESCRIPTION**

The UTC 2N2955 is a silicon PNP transistor in TO-3 metal case. It is intended for power switching circuits, series and shunt regulators, output stages and high fidelity amplifiers.



*Pb-free plating product number:2N2955L

■ **ORDERING INFORMATION**

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2N2955-T30-K	2N2955L-T30-K	TO-3	E	B	C	Bulk

Note: 3: Case

<p>2N2955L-T30-K</p> <pre> graph TD A[2N2955L-T30-K] --- B[] B --- C[] B --- D[] C --- E["(1)Packing Type"] D --- F["(2)Package Type"] E --- G["(1) K: Bulk"] F --- H["(2) T30: TO-3"] G --- I["(3) L: Lead Free Plating, Blank: Pb/Sn"] H --- I </pre>	<p>(1) K: Bulk</p> <p>(2) T30: TO-3</p> <p>(3) L: Lead Free Plating, Blank: Pb/Sn</p>
--	---

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C ,unless otherwise specified)

PARAMETERS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector-Emitter Voltage	V_{CEV}	70	V
Collector Current	I_C	15	A
Collector Peak Current(1)	I_{CM}	15	A
Base Current	I_B	7	A
Base Peak Current(1)	I_{BM}	15	A
Total Dissipation at Ta=25°C	P_D	115	W
Max. Operating Junction Temperature	T_J	+200	°C
Storage Temperature	T_{STG}	-65 ~ 200	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	$I_C=200mA, I_B=0V$	60			V
Collector-Emitter Sustaining Voltage	$V_{CER(SUS)}$	$I_C=0.2A, R_{BE}=100\Omega$	70			V
Collector Cut-off Current	I_{CEO}	$V_{CE}=30V, I_B=0$			0.7	mA
Collector Cut-off Current	I_{CEX}	$V_{CE}=100V, V_{BE(OFF)}=1.5V$ $V_{CE}=100V, V_{BE(OFF)}=1.5V,$ $T_a=150^\circ C$			1.0 5.0	mA
Emitter Cut-off Current	I_{EBO}	$V_{BE}=7V, I_C=0$			5.0	mA
ON CHARACTERISTICS						
DC Current Gain(Note)	h_{FE}	$I_C=4A, V_{CE}=4V,$ $I_C=10A, V_{CE}=4V$	20 5		70	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C=4A, I_B=400mA$ $I_C=10A, I_B=3.3A$			1.1 3.0	V
Base-Emitter On Voltage	$V_{BE(ON)}$	$I_C=4A, V_{CE}=4V$			1.5	V
SECOND BREAKDOWN						
Second Breakdown Collector with Base Forward Biased	$I_{S/b}$	$V_{CE}=60V, T=1.0s, \text{Non-repetitive}$	2.87			A
DYNAMIC CHARACTERISTICS						
Current Gain-Bandwidth Product	f_T	$I_C=0.5A, V_{CE}=10V, f=1MHz$	2.5			MHz
Small-Signal Current Gain	h_{FE}	$I_C=1A, V_{CE}=4V, f=1kHz$	15		120	
Small-Signal Current Gain Cut-off Frequency	fh_{FE}	$I_C=1A, V_{CE}=4V, f=1kHz$	10			kHz

Note(1):Pulse Test: PW 300μs, Duty Cycle 2%

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.